

Filed Stop & Trench Type 1200V IGBT Module

Description

The IGBT Module devices are optimized to reduce losses and switching noise in high frequency power conditioning electrical systems.

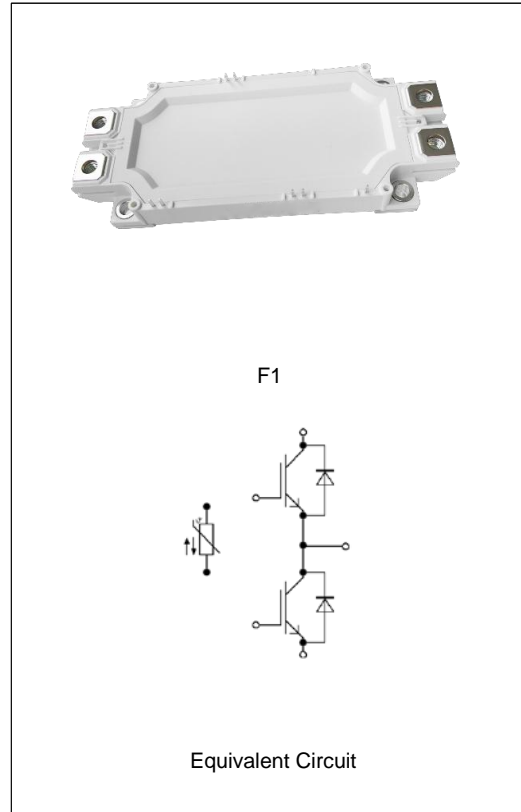
These IGBT Module series are ideally suited for High Power Converters, Motor Drivers, AC and DC servo drive amplifier, UPS where switching losses are significant portion of the total losses and Wind Turbines.

Features

- Low $V_{ce(sat)}$
- $V_{ce(sat)}$ with positive temperature coefficient
- Maximum junction temperature 150°C
- High Power Density
- Isolated Base Plate
- Standard Housing

Applications

- High Power Converters
- Motor Drivers
- AC and DC servo drive amplifier
- UPS (Uninterruptible Power Supplies)
- Wind Turbines



IGBT Characteristics

Absolute Maximum Ratings

Symbol	Parameter	Conditions	Value	Unit
V_{CES}	Collector to Emitter Voltage	$T_{vj}=25^{\circ}\text{C}$	1200	V
I_C	Continuous Collector Current	$T_C=25^{\circ}\text{C}, T_{vjmax}=150^{\circ}\text{C}$	450	A
		$T_C=100^{\circ}\text{C}, T_{vjmax}=150^{\circ}\text{C}$	300	
I_{CRM}	Repetitive Peak Collector Current	$t_p=1\text{ms}$	600	A
V_{GES}	Gate-Emitter Voltage		± 20	V
P_{tot}	Total Power Dissipation	$T_C=25^{\circ}\text{C}, T_{vjmax}=150^{\circ}\text{C}$	2100	W

Characteristic Values

Symbol	Parameter	Conditions	Value			Unit
			Min.	Typ.	Max.	
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$V_{GE}=V_{CE}, I_C=1mA, T_{vj}=25^{\circ}C$	5.0	5.22	6.5	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=300A, V_{GE}=15V, T_{vj}=25^{\circ}C$		1.90	2.30	V
		$I_C=300A, V_{GE}=15V, T_{vj}=125^{\circ}C$		2.10		
		$I_C=300A, V_{GE}=15V, T_{vj}=150^{\circ}C$		2.15		
I_{CES}	Collector-Emitter Cut-off Current	$V_{CE}=1200V, V_{GE}=0V, T_{vj}=25^{\circ}C$			3.0	mA
I_{GES}	Gate-Emitter leakage current	$V_{CE}=0V, V_{GE}=20V, T_{vj}=25^{\circ}C$			400	nA
Q_G	Gate Charge	$V_{GE}=\pm 15V$		3.45		uC
C_{ies}	Input Capacitance	$V_{CE}=25V, V_{GE}=0V, f=1MHz, T_{vj}=25^{\circ}C$		29.5		nF
C_{res}	Reverse Transfer Capacitance			1.60		nF
R_{gint}	Internal Gate Resistance	$T_{vj}=25^{\circ}C$		1.8		Ω
$t_{d(on)}$	Turn-on Delay Time	$I_C=300A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=1.5\Omega$ $T_{vj}=25^{\circ}C$		320		ns
t_r	Rise Time			150		ns
$t_{d(off)}$	Turn-off Delay Time			700		ns
t_f	Fall Time			105		ns
E_{on}	Energy Dissipation During Turn-on Time			48.5		mJ
E_{off}	Energy Dissipation During Turn-off Time			26.5		mJ
$t_{d(on)}$	Turn-on Delay Time		$I_C=300A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=1.5\Omega$ $T_{vj}=150^{\circ}C$		340	
t_r	Rise Time			180		ns
$t_{d(off)}$	Turn-off Delay Time			720		ns
t_f	Fall Time			200		ns
E_{on}	Energy Dissipation During Turn-on Time			70.0		mJ
E_{off}	Energy Dissipation During Turn-off Time			38.5		mJ
I_{sc}	SC Data	$T_p \leq 10\mu s, V_{GE} \leq 15V, T_{vj} = 150^{\circ}C, V_{cc} = 800V, V_{CEM} \leq 1200V$			1450	

Diode Characteristics

Absolute Maximum Ratings

Symbol	Parameter	Conditions	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	$T_{vj}=25^{\circ}\text{C}$	1200	V
I_F	Continuous DC Forward Current		300	A
I_{FRM}	Repetitive Peak Forward Current	$t_p=1\text{ms}$	600	A

Characteristic Values

Symbol	Parameter	Conditions	Value			Unit
			Min.	Typ.	Max.	
V_F	Forward Voltage	$I_F=300\text{A}, T_{vj}=25^{\circ}\text{C}$		1.90	2.40	V
		$I_F=300\text{A}, T_{vj}=125^{\circ}\text{C}$		1.75		
		$I_F=300\text{A}, T_{vj}=150^{\circ}\text{C}$		1.70		
Q_{rr}	Recovered Charge	$I_F=300\text{A}$ $V_R=600\text{V}$ $-di_F/dt=5000\text{A/us}$ $T_{vj}=25^{\circ}\text{C}$		48		uC
I_{rm}	Peak Reverse Recovery Current			275		A
E_{rec}	Reverse Recovery Energy			21.5		mJ
Q_{rr}	Recovered Charge	$I_F=300\text{A}$ $V_R=600\text{V}$ $-di_F/dt=5000\text{A/us}$ $T_{vj}=150^{\circ}\text{C}$		84		uC
I_{rm}	Peak Reverse Recovery Current			325		A
E_{rec}	Reverse Recovery Energy			45.0		mJ

NTC- Thermistor

Characteristic Values

Symbol	Parameter	Conditions	Value			Unit
			Min.	Typ.	Max.	
R_{25}	Rated resistance	$T_C=25^{\circ}\text{C}$		5.0		k Ω
$\Delta R/R$	Deviation of R_{100}	$T_C=100^{\circ}\text{C}, R_{100}=493\Omega$	-5		5	%
P_{25}	Power dissipation	$T_C=25^{\circ}\text{C}$			18.0	mW
$B_{25/50}$	B-Value	$R_2= R_{25}\exp[B_{25/50}(1/T_2-1/(298, 15K))]$		3370		K
$B_{25/80}$		$R_2= R_{25}\exp[B_{25/80}(1/T_2-1/(298, 15K))]$		3415		
$B_{25/100}$		$R_2= R_{25}\exp[B_{25/100}(1/T_2-1/(298, 15K))]$		3440		

Module Characteristics $T_c=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Conditions	Value			Unit
			Min.	Typ.	Max.	
V_{isol}	Isolation voltage	$t=1\text{min}, f=50\text{Hz}$	2500			V
$T_{\text{vj op}}$	Operating Junction Temperature		-40		150	$^\circ\text{C}$
T_{stg}	Storage Temperature		-40		125	$^\circ\text{C}$
L_{CE}	Stray Inductance			20		nH
$R_{\text{cc}+\text{EE}}$	Module Lead Resistance, Terminal to Chip	$T_c=25^\circ\text{C}$, per switch		1.3		$\text{m}\Omega$
R_{thJC}	Thermal Resistance Junction to Case	per IGBT			0.06	K/W
		per Diode			0.10	
R_{thCS}	Thermal Resistance Case to Sink	per IGBT		0.03		K/W
		per Diode		0.04		
		per Module		0.009		
M_s	Module-to-Sink Torque (M6)		3.0		6.0	N-m
G	Weight of Module			348		g

Typical Performance Characteristics

Fig. 1. Typical Output Characteristics

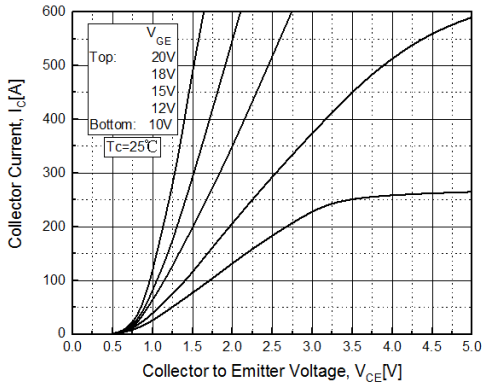


Fig. 2. Typical Output Characteristics

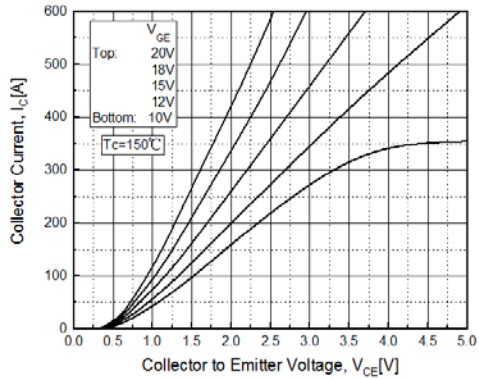


Fig. 3. Typical Saturation Voltage Characteristics

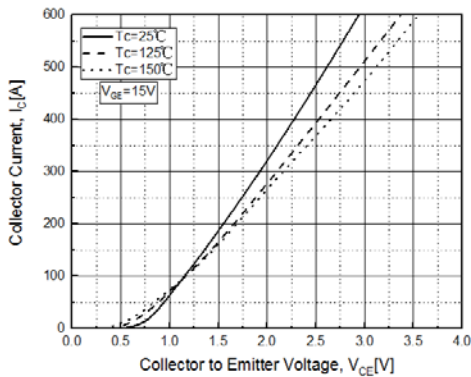


Fig. 4. Typical Transfer Characteristics

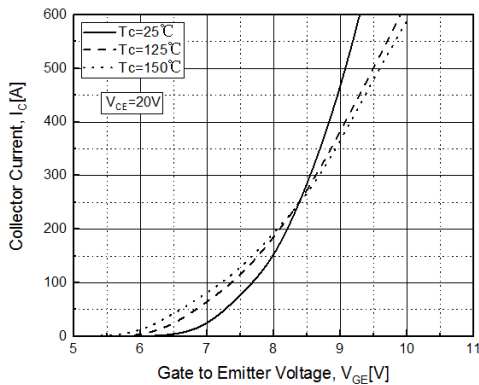


Fig. 5. Switching Characteristics vs. R_G

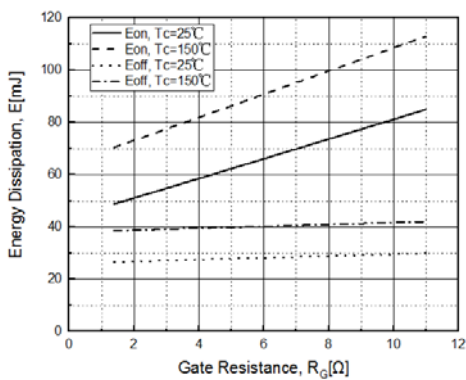
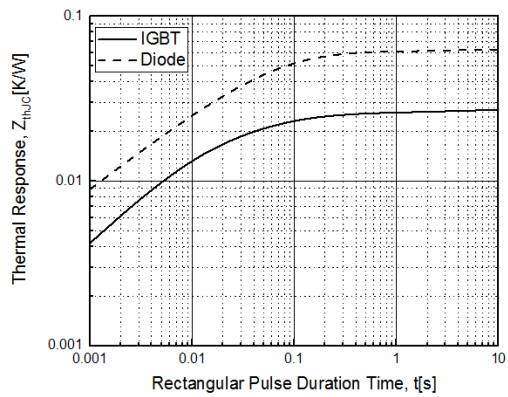


Fig. 6. Transient Thermal Impedance



Typical Performance Characteristics

Fig. 7. Forward Characteristics of Diode

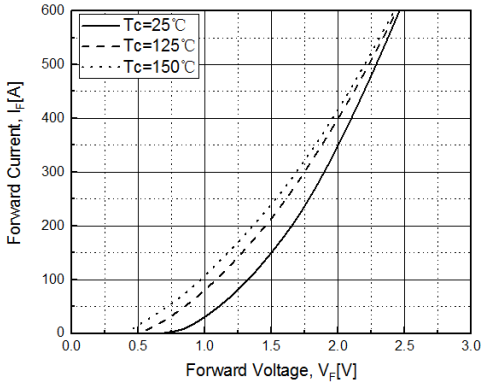


Fig. 8. Reverse Recovery Loss Characteristics vs. R_G

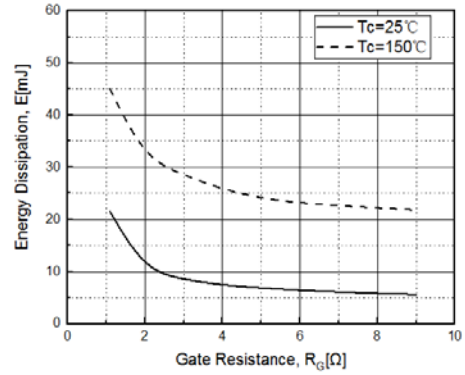


Fig. 9. Reverse Bias Safe Operating Area

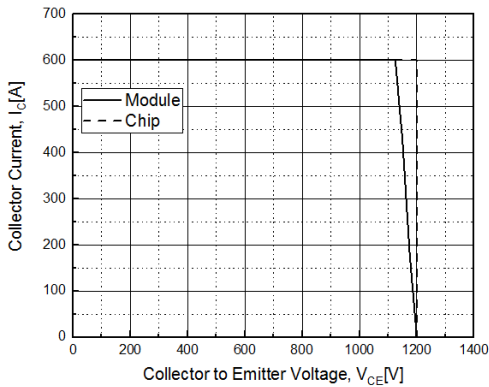
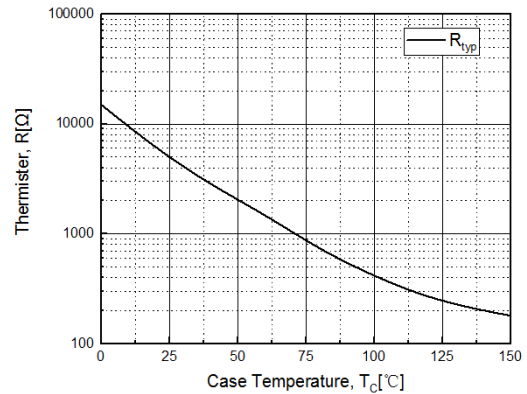
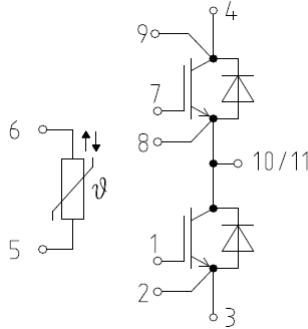


Fig. 10. NTC-Thermistor-temperature characteristic



Circuit Diagram



Package Dimensions

